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Patent Application

Applicant(s): M.A. Shibib et al.

Case:

37-6

Serial No.:

10/688,231

Filing Date:

October 17, 2003

Group:

2811

Examiner:

To Be Assigned

Title:

Metal-Oxide-Semiconductor Device

Having Improved Performance and Reliability

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §§1.56, 1.97 and 1.98, Applicants' attorney wishes to bring to the attention of the Patent and Trademark Office the following document listed on the accompanying Form PTO-1449: C.S. Kim et al., "Trenched Sinker LDMOSFET (TS-LDMOS) Structure for High Power Amplifier Application above 2 GHz," IEEE, IEDM, pp. 40.2.1-10.2.4, 2001. A copy of the listed document is enclosed.

It is believed that there is no fee due in conjunction with the filing of this Information Disclosure Statement. In the event of non-payment or improper payment of a required fee, the Commissioner is authorized to charge or to credit Ryan, Mason & Lewis, LLP Deposit Account No. 50-0762 as required to correct the error.

The filing of this Information Disclosure Statement shall not be construed as a representation that a search has been made, or as an admission that the information cited is considered to be material to patentability, or as a representation that no other material information exists.

Respectfully submitted,

Date: February 2, 2004

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FORM PTO-1449 (MODIFIED)

LIST OF PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT



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Case: 37-6

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INITIAL	DOCUMENT NO.	DATE	NAME		CLASS/SUBCLASS	IF APPROPRIATE
						
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Examiner					Date Considere	ed

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.